

THEORETICAL STUDIES OF  $\text{Sr}_2\text{VO}_4$ , A CHARGE CONJUGATE ANALOG OF  $\text{La}_2\text{CuO}_4$ .

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We have used local (spin) density theory to study the atomic geometry and electronic structure of  $\text{K}_2\text{NiF}_4$ -structure  $\text{Sr}_2\text{VO}_4$ . The calculations correctly predict the  $\text{Cu-O}_2$  distance, reflecting a negative Jahn-Teller distortion (relative to  $\text{La}_2\text{CuO}_4$ ). The oxygen p bands are filled, leaving one d electron per V, but in the paramagnetic phase three bands cross  $E_F$  rather than having a single half-filled band. We find a ferromagnetic instability within local spin density theory, rather than the antiferromagnetic insulator seen experimentally.

Since the only known compounds having superconducting transition temperature  $T_c$  above 35 K contain  $\text{CuO}_2$  layers as a basic structural unit, there is strong interest in determining whether there are new systems without  $\text{CuO}_2$  layers which contain high  $T_c$  materials. Since these systems are hole conductors, at least in the sense that the broad complex of Cu-O valence bands are nearly filled, an alternative is to look for charge conjugate counterparts which are electron conductors. The  $\text{Nd}_2\text{CuO}_4$ -based materials have Hall coefficients of opposite sign to the other Cu-O systems, but the overall electronic structure is very similar.

An unusually interesting material is  $\text{Sr}_2\text{VO}_4$ , for which formal valence counting leads to  $(\text{Sr}^{2+})_2\text{V}^{4+}(\text{O}^{2-})_4$ , containing only one d electron per V outside closed shells. This compound exists in the  $\text{K}_2\text{NiO}_4$  structure, and is tentatively identified as a narrow gap ( $<0.1$  eV) antiferromagnetic (AFM) insulator ( $T_N < 100$  K). The AFM state is not unexpected, since the single d electron per V can be expected to

lead to a half-filled d band and the accompanying AFM instability.

We have applied the full-potential Linearized Augmented Plane Wave method to compute the electronic band structure and total energy of  $\text{Sr}_2\text{VO}_4$ , using the Hedin-Lundqvist (von Barth-Hedin) exchange-correlation functionals for the paramagnetic (spin-polarized) cases. The experimental values  $a=3.827$  Å,  $c=12.574$  Å, and  $z_{\text{Sr}}=0.355$  were used. Total energy studies determined the minimum at a  $\text{Vu-O}_2$  distance of 2.01 Å, subsequently verified by neutron diffraction studies. Although this distance is 5% larger than the  $\text{Vu-O}_{xy}$  distance of 1.91 Å, it is much smaller than the 2.4 Å distance in  $\text{La}_2\text{CuO}_4$ , consistent with a JT effect of opposite sign.

Self-consistent solutions indicated the ferromagnetic (FM) state is more stable than the paramagnetic state by 6.1 mRy/cell. In the PM case we find 12 filled O p bands 5 eV wide, separated by 1 eV from the valence V d bands containing one electron per V atom (Fig. 1). However, there are three bands crossing

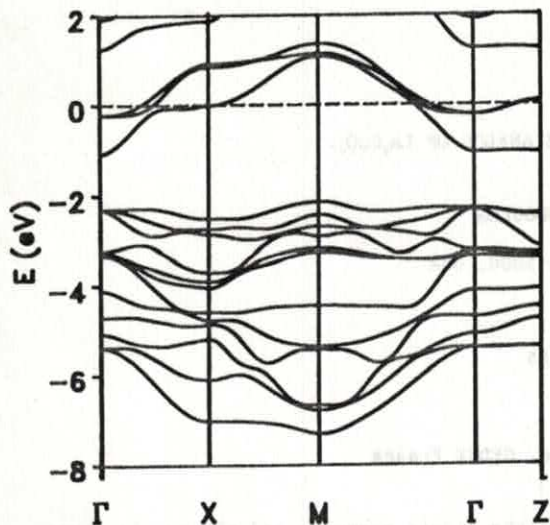


Figure 1. Paramagnetic bands of  $\text{Sr}_2\text{VO}_4$ . Here  $X=(1,0,0)\pi/a$ ,  $M=(1,1,0)\pi/a$ .

the Fermi level  $E_F$ , two light mass bands and a heavy mass band leading to a highly anisotropic FS and a large peak at  $E_F$ . This peak promotes the FM instability, the resulting d band exchange splitting being 0.7 eV. The FM spin-resolved partial densities of states are shown in Fig. 2; note there is no appreciable polarization of the O p states.

We have made careful attempts (including extensive tests of k-point sampling) without success, to obtain an AFM solution of the same symmetry<sup>3</sup> as is found in  $\text{La}_2\text{CuO}_4$ . The FS is neither simple nor two dimensional, due to the considerable dispersion of bands at  $E_F$  along the c direction, which leads to a pair of closed, three dimensional spheroids as well as a more complex shaped FS, each centered at  $\Gamma$ .

The 5 eV bandwidth of the O p complex is not surprising, since McMahan et al.<sup>4</sup> showed that direct O-O overlap leads to a similar bandwidth in  $\text{La}_2\text{CuO}_4$ . The dispersion of the V d bands (greater than 4 eV) is somewhat more

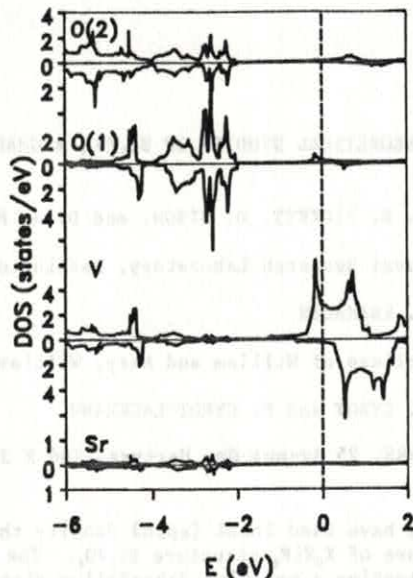


Figure 2. Local DOS for the FM case: upper lines, majority; lower lines, minority.

surprising, since the d states are well separated from one another and interaction must proceed through the intermediate O p states, which are lower in energy and filled. Nevertheless, substantial p-d hybridization exists. Crystal field splittings can also contribute to the total d band width; however, since the  $\text{CuO}_6$  octahedron is not far from cubic, such contributions may be secondary.

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